

In th Sp cification

Please amend the title as follows:

B¹ ~~Microelectronic Device Fabricating Method, Integrated Circuit, and Intermediate Construction Having an Edge Defined Feature~~

Please amend the Related Patent Data section on page 1 of the specification as follows:

B² This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/561,794 filed on May 1, 2000 which is a divisional of U.S. Patent Application Serial No. ~~09/444,280~~ 6,232,229 filed on November 19, 1999.

Please amend the abstract on page 42 of the specification as follows:

B³ ~~A microelectronic device fabricating method includes providing a substrate having a beveled portion and forming a layer of structural material on the beveled portion. Some of the structural material can be removed from the beveled portion by anisotropic etching to form a device feature from the structural material. The device feature can be formed on the beveled portion as with a pair of spaced, adjacent barrier material lines that are substantially void of residual shorting stringers extending therebetween. Structural material can be removed from the beveled portion to form an edge defined feature on a substantially perpendicular edge of the substrate. The beveled portion and perpendicular edge can be part of a mandril. The mandril can be removed from the substrate after forming the edge defined feature. An intermediate construction of an integrated circuit~~

8³ includes a semiconductive substrate and a raised mandril over the substrate. The raised mandril may be raised out from the substrate and have at least one edge substantially perpendicular to the substrate and at least one beveled edge. A layer of structural material may form an edge defined feature on the at least one perpendicular edge.
